

SEMICONDUCTOR

BC214LB

PNP General Purpose Amplifier

- This device is deisgned for use as general purpose amplifiers and switches requiring collector currents to 300mA.
- Sourced from process 68.



1. Emitter 2. Collector 3. Base

Absolute Maximum Ratings* Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{CBO}	Collector-Base Voltage	-45	V
V _{EBO}	Emitter-Base Voltage	-5.0	V
I _C	Collector Current (DC) Continuous	-500	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Electrical Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characte	eristics				
V _{(BR)CEO}	Collector-Emitter Voltage	$I_{\rm C} = -2mA, I_{\rm B} = 0$	-30		V
V _{(BR)CBO}	Collector-Base Voltage	$I_{\rm C} = -10 \mu {\rm A}, \ I_{\rm E} = 0$	-45		V
V _{(BR)EBO}	Emitter-Base Voltage	$I_{\rm E} = -10\mu A, I_{\rm C} = 0$	-5.0		V
I _{CBO}	Collector Cut-off Current	$V_{CB} = -30V, I_E = 0$		-15	nA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -4V, I_{C} = 0$		-15	nA
On Characte	eristics *				
h _{FE}	DC Current Gain	$V_{CE} = -5V, I_{C} = -2mA$	140	400	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_{C} = -10$ mA, $I_{B} = -0.5$ mA $I_{C} = -100$ mA, $I_{B} = -5$ mA		-0.25 -0.6	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_{\rm C} = -100$ mA, $I_{\rm B} = -5$ mA		-1.1	V
V _{BF} (on)	Base-Emitter On Voltage	$V_{CF} = -5V, I_{C} = -2mA$	-0.6	-0.72	V
Small Signa	I Characteristics		I		
f _T	Current gain Bandwidth Product	$V_{CE} = -5V, I_{C} = -10mA$ f = 100MHz	200		MHz
NF	Noise Figure	$V_{CE} = -5V$, $I_C = -200\mu A$ $R_G = 2k\Omega$, f = 15.7KHz		2.0	dB
h _{fe}	Small Signal Current Gain	$I_{C} = -2mA, V_{CE} = -5V$ f = 1KHz	200	400	
C _{OB}	Output Capacitance	V _{CB} = -10V, f = 1MHz		10	pF

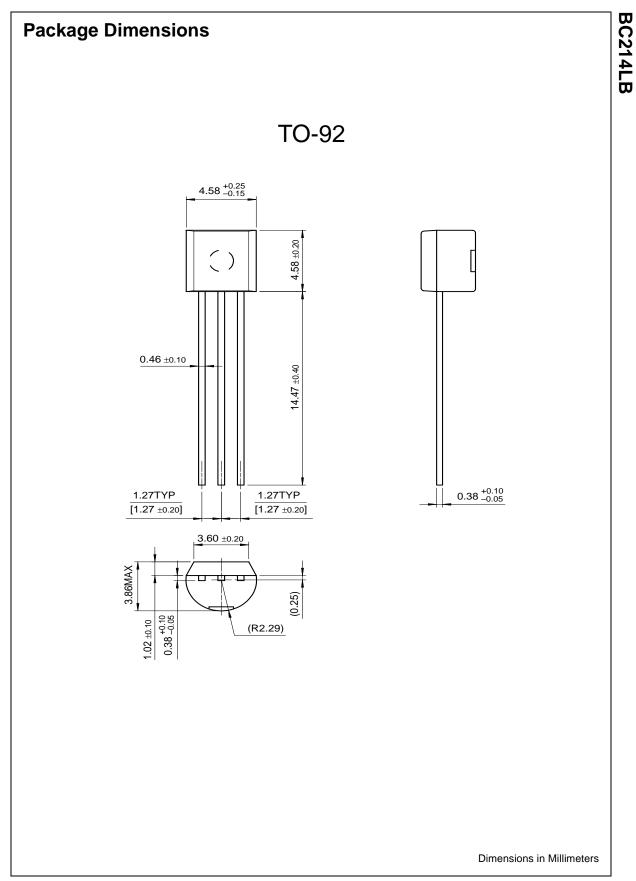
Pulse Test: Pulse Width $\leq 300 \mu s, \, Duty \, Cycle \leq 2.0\%$

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Symbol	Parameter	Max.	Units
D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
R _{0JA}	Thermal Resistance, Junction to Ambient	200	°C/W

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FACT™	ISOPLANAR™	OPTOLOGIC®	SMART START™	
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The Power Franc	hise™	PACMAN™	Stealth™	
Programmable A	ctive Droop™	POP™	SuperSOT™-3	

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